

AP5N10S

N-Channel Power MOSFET

Description

The AP5N10S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. It is ESD protected.

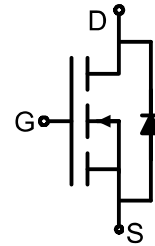
General Features

- | V_{DSS} | $R_{DS(ON)}$
@ 10V (typ) | I_D |
|-----------|-----------------------------|-------|
| 100V | 115mΩ | 5A |

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply
- Motor control



Schematic diagram



SOT23-3L

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	5	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	21	A
Maximum Power Dissipation	P_D	5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	41.7	°C/W
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Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	110	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$	-	-	800	nA

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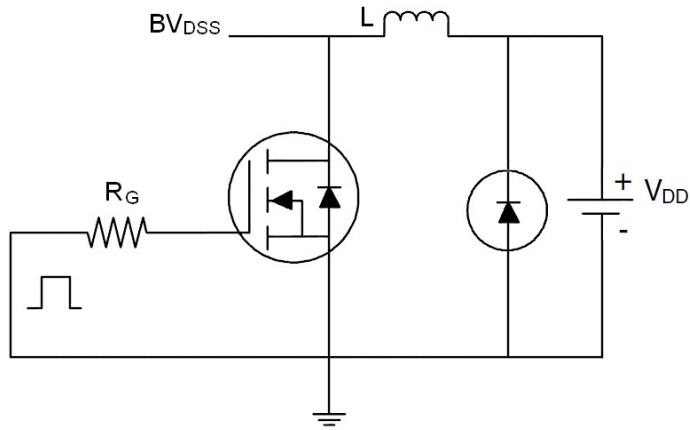
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.8	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3A$		115	145	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=2.9A$	-	8	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	210	-	PF
Output Capacitance	C_{oss}		-	30	-	PF
Reverse Transfer Capacitance	C_{rss}		-	14	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=5A, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$	-	15	-	nS
Turn-on Rise Time	t_r		-	3.4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	21	-	nS
Turn-Off Fall Time	t_f		-	3.1	-	nS
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=5A,$ $V_{GS}=10V$		4.5		nC
Gate-Source Charge	Q_{gs}		-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	1.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=6A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	5	A

Notes:

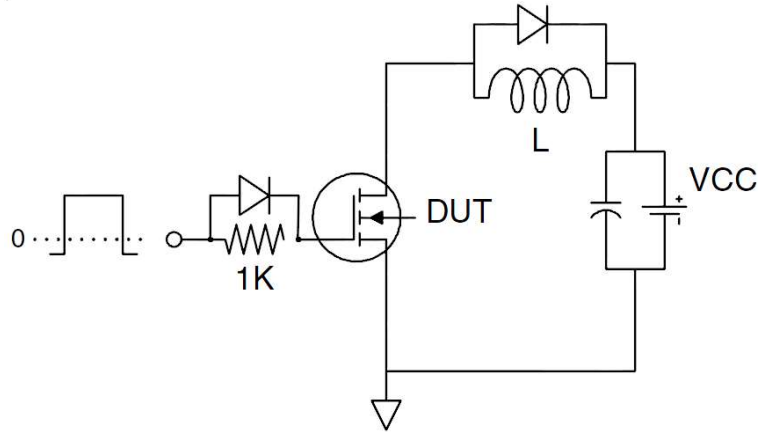
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

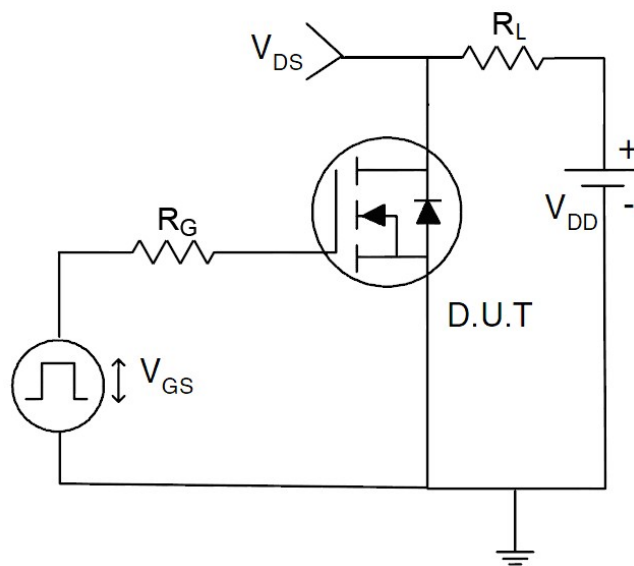
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



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Typical Electrical and Thermal Characteristics (curves)

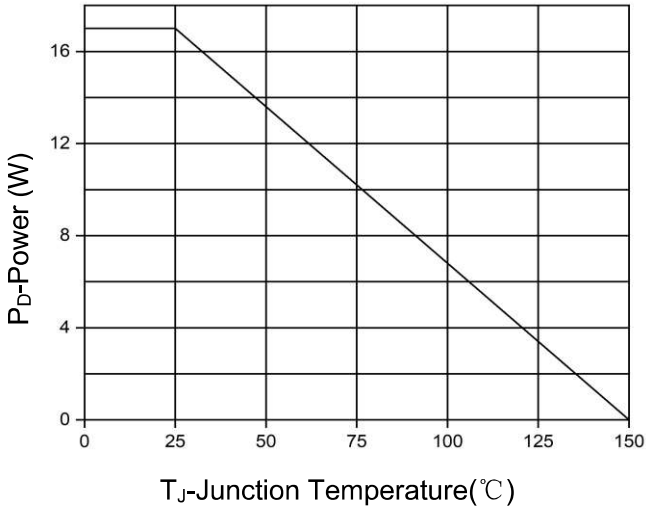


Figure 1. Power Dissipation

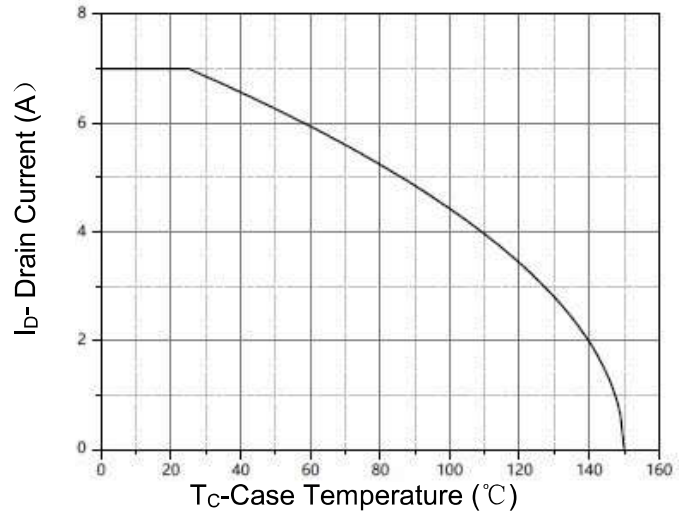


Figure 2. Drain Current

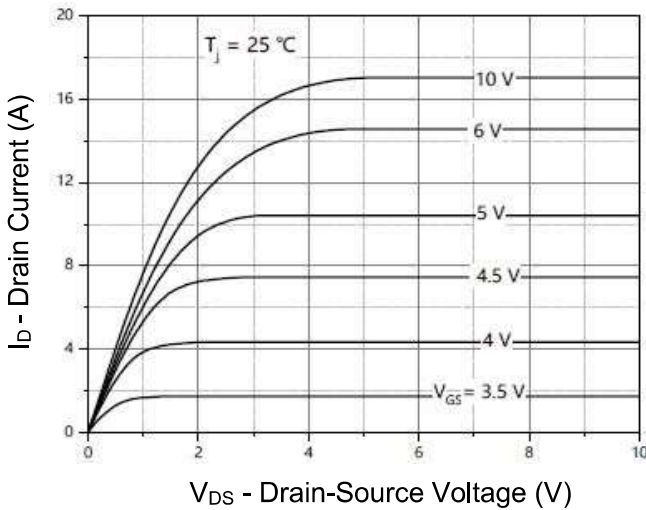


Figure 3. Output characteristics

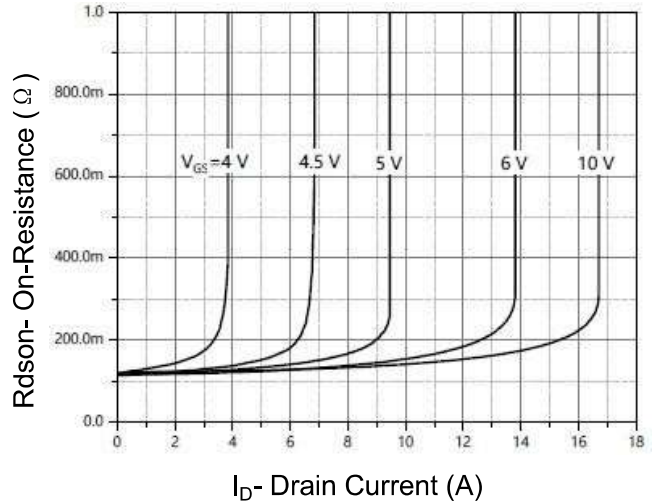


Figure 4. Drain-Source On-state resistance

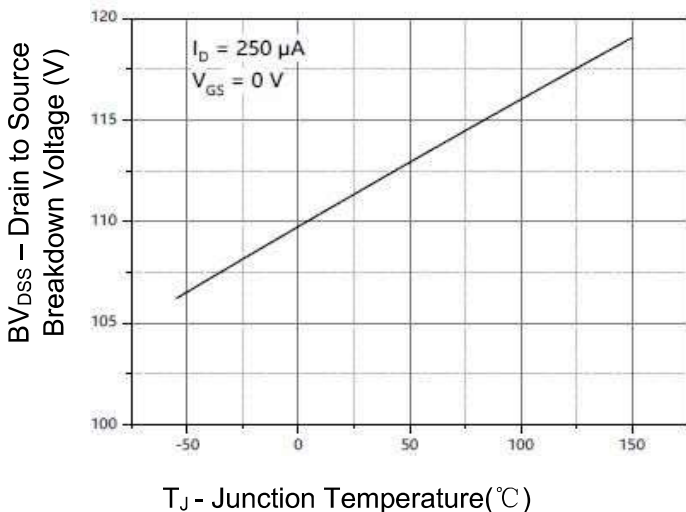


Figure 5. Drain-source breakdown voltage

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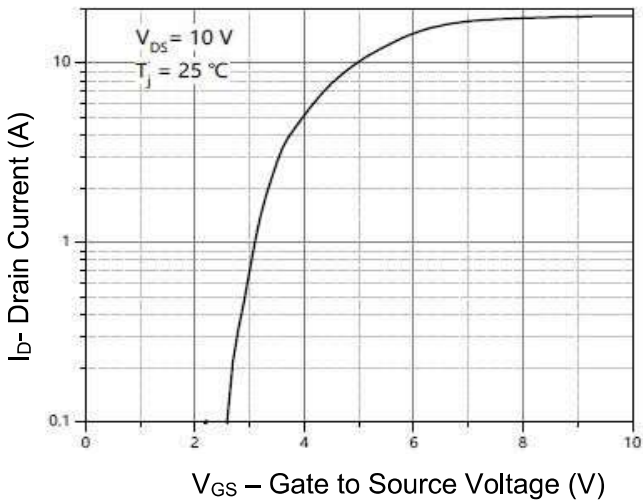


Figure 6. Transfer Characteristics

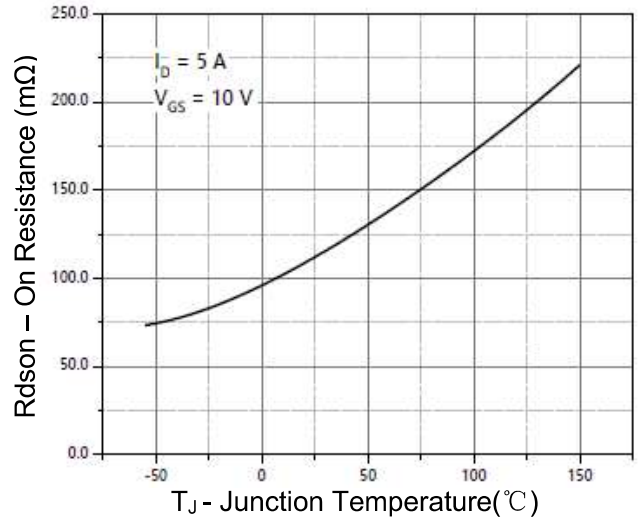


Figure 7. Drain-Source On-State Resistance

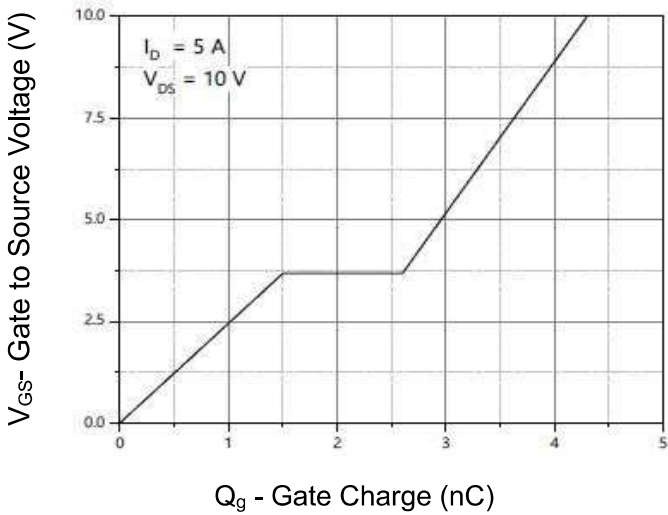


Figure 8. Gate Charge

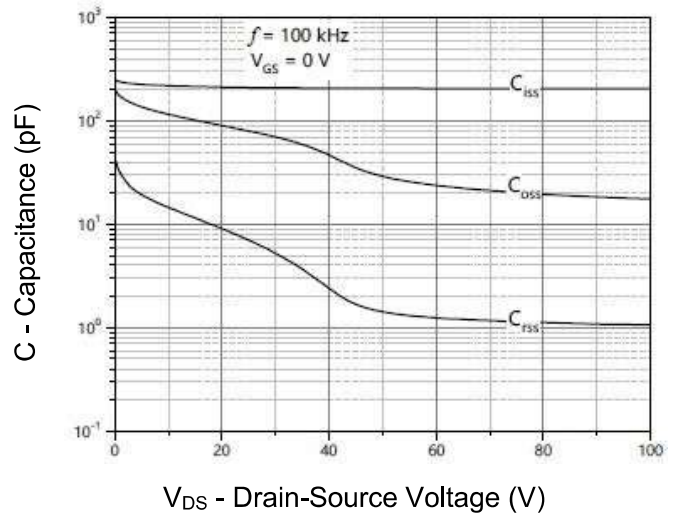


Figure 9 . Capacitance vs Vds

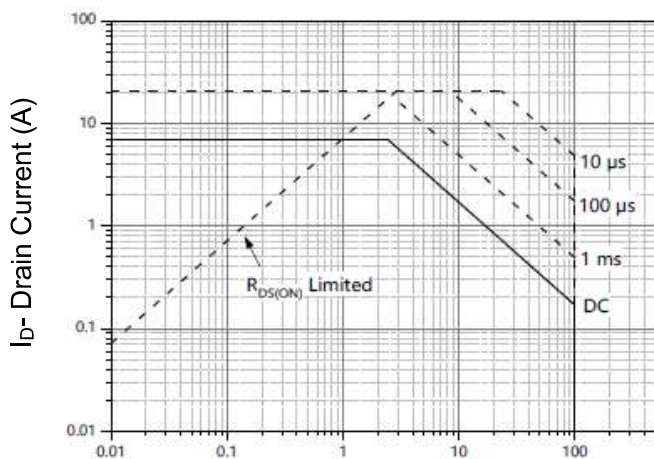


Figure 10. Safe Operation Area

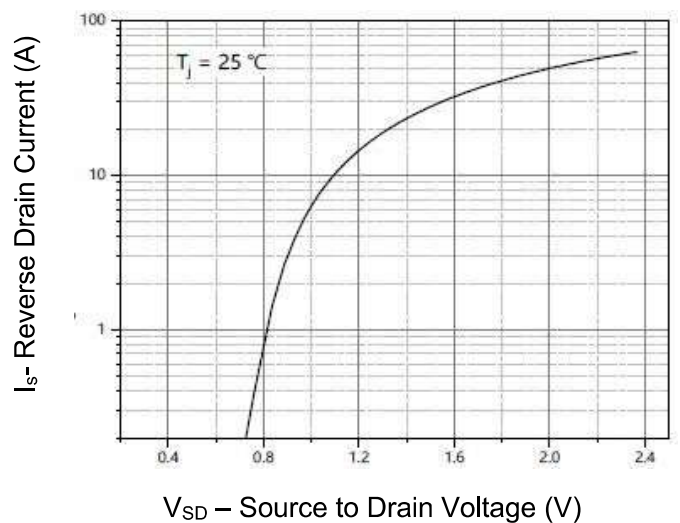
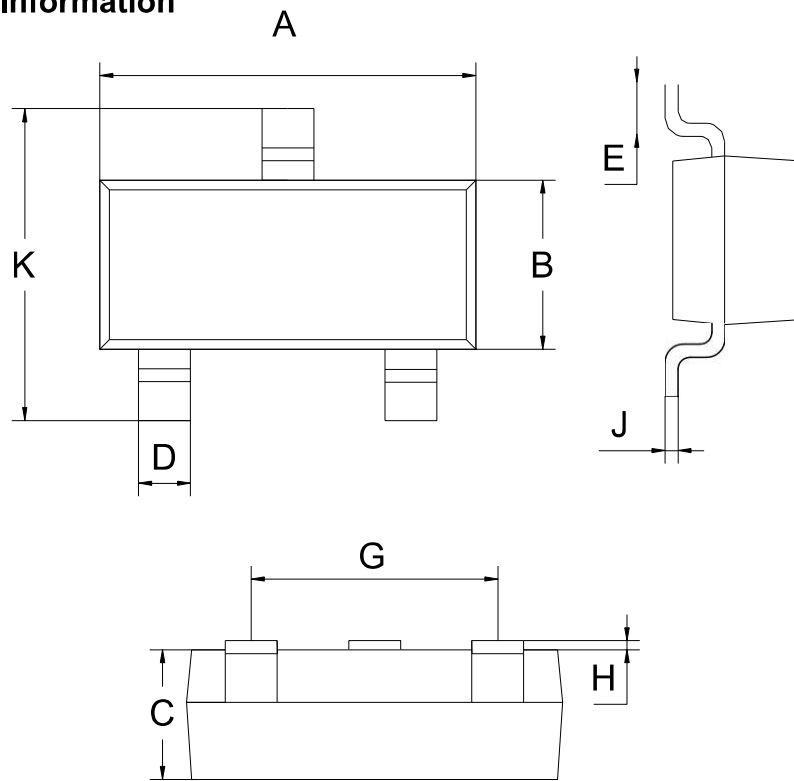


Figure 11. Source- Drain Diode Forward

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SOT-23-3L Package Information



SOT-23-3L			
Dim	MIN	NOM	MAX
A	2.80	2.90	3.00
B	1.50	1.60	1.70
C	1.00	1.10	1.20
D	0.30	0.40	0.50
E	0.25	0.40	0.55
G	1.90		
H	0.00	-	0.10
J	0.047	0.127	0.207
K	2.60	2.80	3.00
All Dimensions in mm			